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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/650,046	08/28/2003	Toru Takayama	0756-7193	7230
31780	7590	01/26/2007	EXAMINER	
ERIC ROBINSON PMB 955 21010 SOUTHBANK ST. POTOMAC FALLS, VA 20165			NGUYEN, THANH T	
			ART UNIT	PAPER NUMBER
			2813	
SHORTENED STATUTORY PERIOD OF RESPONSE		MAIL DATE	DELIVERY MODE	
3 MONTHS		01/26/2007	PAPER	

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

Office Action Summary

Application No.

10/650,046

Applicant(s)

TAKAYAMA ET AL.

Examiner

Thanh T. Nguyen

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 03 November 2006.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 3-5,8,13,18,23,28,33,36-43,45,47-57 and 74-80 is/are pending in the application.
- 4a) Of the above claim(s) none is/are withdrawn from consideration.
- 5) ☒ Claim(s) 36-43,45 and 47-57 is/are allowed.
- 6) ☒ Claim(s) 3-5,8,13,18,23,28,33 and 74-80 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
- ☐ Certified copies of the priority documents have been received.
 - ☐ Certified copies of the priority documents have been received in Application No. _____.
 - ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|--|---|
| 1) <input type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____ |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3) <input checked="" type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date <u>11/3/06</u> . | 6) <input type="checkbox"/> Other: _____ |

DETAILED ACTION

Request for Continued Examination

The request filed on 11/15/05 for a Request for Continued Examination (RCE) under 37 CFR 1.114 is acceptable and an RCE has been established. An action on the RCE follows.

Information Disclosure Statement

The information disclosure statement filed on 11/3/06 has been considered.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 3-5, 8, 13, 28, 33, 74, 76-77, 79-80 are rejected under 35 U.S.C. 103(a) as being unpatentable over Joo et al. (U.S. Patent Publication No. 2002/0056839) in view of Yamazaki et al. (U.S. Patent Publication No. 2001/0049163A1).

Referring to figures 1-9f, Joo et al. teaches a manufacturing method for a semiconductor device comprising:

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Forming at least first and second semiconductor layers (33, amorphous silicon) that are divided from each other in an island-like shape over a substrate surface having an insulating surface (32, silicon oxide, see figures 3a), wherein each of the first and second semiconductor layers includes a region to become at least a channel region of a thin film transistor (see paragraph# 26, figure 3a);

Forming a conductive layer (35, doped polysilicon) covering an entire surface of each of the first and second semiconductor layers (33) with an insulating layer (34) interposed the between (see figure 3b, paragraph# 28); and

Selectively heating the first and second semiconductor layer by irradiating an incoherent electromagnetic wave within a wavelength band ranging at least from a visible light band to an infrared band to thereby conducting heat treatment on the first and second semiconductor layers and the insulating layer, wherein the conductive layer extends beyond each periphery of the first and second semiconductor layers at least when the selected heating of the first and second semiconductor layers is performed (see paragraphs# 32, figure 3f). It is inherent that heating the conductive layer, the semiconductor layers and the insulating layer will also heated.

Regarding to claims 8, 76, substrate is a glass substrate (see paragraph# 23).

Regarding to claims 13, 77, the substrate is quartz or sapphire (see paragraph# 23).

Regarding to claims 28, 79, forming a second conductive layer (36, nickel, see paragraph# 29) on the conductive layer (35) and forming a part of a gate electrode (35) using the conductive layer (35, see figures 3c-3d(1)).

Regarding to claim 74, a manufacturing method for a semiconductor device comprising:

Forming a semiconductor layer (33, amorphous silicon) over a substrate (30);

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Forming an insulating layer (34, silicon oxide) over the semiconductor layer (33);

Forming a conductive layer (35) over the semiconductor layer with the insulating layer (34) interposed there between;

Selectively heating the semiconductor layer by using a heat source capable of radiating an incoherent electromagnetic wave within a wavelength band ranging at least a visible light band to an infrared band wherein the conductive layer extends beyond a periphery of the semiconductor layer at least when the selective heating of the semiconductor layer is performed (see paragraphs# 32, figure 3f). It is inherent that heating the conductive layer, the semiconductor layers and the insulating layer will also heated.

Yamazaki et al. teaches etching the conductive layer after the selective heating the first and second semiconductor layers to form at least first and second gate electrodes over the first and second semiconductor islands, respectively (see figures 2a, 16, meeting claims 3, 4, 74), the incoherent electromagnetic wave is irradiated for 30-300 seconds (see paragraph# 254, meeting claim 5), the heat treatment is performed at a temperature not less than a distortion point of the substrate (see paragraph# 254, 294, heating at the temperature 700-1000°C which is greater than 700°C (at the distortion point), meeting claims 33, 80).

Therefore, it would have been obvious to a person of ordinary skill in the requisite art at the time of the invention was made would form plurality of semiconductive island, etching the conductive layer after the selective heating for 30-300 second at the temperature greater than distortion point of the substrate in process of Joo et al. as taught by Yamazaki et al. because forming plurality of semiconductor island would provide plurality of thin film transistors,

etching the conductive layer to form the gate electrode, heating to crystallized the layer as well as to activate the impurity added to the film.

Claims 18, 23, 75, 78 are rejected under 35 U.S.C. 103(a) as being unpatentable over Joo et al. (U.S. Patent Publication No. 2002/0056839) in view of Yamazaki et al. (U.S. Patent Publication No. 2001/0049163A1) as applied to claims 3-5, 8, 13, 28, 33, 74, 76-77, 79-80 above in view of Yamazaki et al. (U.S. Patent Publication No. 2002/0000551).

Joo et al. in view of Yamazaki et al. teaches a method of forming a semiconductor device. However, Yamazaki does not teach the substrate has a transmittance of 50 % or higher with respect to the electromagnetic wave within the wavelength band, forming a first conducting film comprising metal nitride and forming a second conducting film over the first conducting film as a part of the gate electrode.

Regarding to claims 23, 78, the conductive film comprises metal nitride (see paragraph# 245).

Therefore, it would have been obvious to a person of ordinary skill in the requisite art at the time of the invention was made to form a quartz substrate in process of Joo et al. as taught by Yamazaki et al. in order for light transparent or to form an insulating substrate, forming the conductive film on the gate insulating film in order to form gate electrode for TFT device.

Regarding to claims 18, 75, it would have been obvious to a person of ordinary skill in the requisite art at the time of the invention was made to optimize the a transmittance of 50 % or higher with respect to the electromagnetic wave within the wavelength band, since it has been held that where the general conditions of a claim are disclosed in the prior art (i.e.- a

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transmittance of 50 % or higher with respect to the electromagnetic wave within the wavelength band), discovering the optimum or workable ranges involves only routine skill in the art. In re Aller, 105 USPQ 233 (CCPA 1955).

The specification contains no disclosure of either the critical nature of the claimed arrangement (i.e.- a transmittance of 50 % or higher with respect to the electromagnetic wave within the wavelength band) or any unexpected results arising therefrom. Where patentability is said to be based upon particular chosen limitations or upon another variable recited in a claim, the applicant must show that the chosen limitations are critical. In re Woodruff, 919 F.2d 1575, 1578 (FED. Cir. 1990).

Therefore, it would have been obvious to a person of ordinary skill in the requisite art at the time of the invention was made to form the substrate has a transmittance of 50 % or higher with respect to the electromagnetic wave within the wavelength band in process of Joo et al. in order to optimize the process.

Allowable Subject Matter

Claims 36-43, 45, 47-57 are allowed. Because none of the prior art alone or in combination teaches a heating the substrate by radiation heating from a first heat source and form the layers on the substrate, then heating the layer by using a second heat source for radiating the incoherent electromagnetic wave.

Conclusion

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thanh Nguyen whose telephone number is (571) 272-1695, or by Email via address Thanh.Nguyen@uspto.gov. The examiner can normally be reached on Monday-Thursday from 6:00AM to 3:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead, Jr., can be reached on (571) 272-1702. The fax phone number for this Group is (571) 273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pairedirect.uspto.gov>. Should you have questions on access to thy Private PAIR system, contact the Electronic Business center (EBC) at 866-217-9197 (toll-free).



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TTN